

### < X/Ku band internally matched power GaAs FET >

# MGFK39V4045

14.0 - 14.5 GHz BAND / 8W

#### **DESCRIPTION**

The MGFK39V4045 is an internally impedance-matched GaAs power FET especially designed for use in 14.0 – 14.5 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

#### **FEATURES**

Internally matched to 50(ohm) system

- Flip-chip mounted
  High output power
  - P1dB=8W (TYP.) @f=14.0 14.5GHz
- High linear power gain
  - ĞLP=5.5dB (TYP.) @f=14.0 14.5GHz
- High power added efficiency
  - P.A.E.=20% (TYP.) @f=14.0 14.5GHz

### **APPLICATION**

• 14.0 - 14.5 GHz band power amplifiers

#### **QUALITY GRADE**

• IG

#### RECOMMENDED BIAS CONDITIONS

• VDS=10V • ID=2.4A Refer to Bias Procedure

### **Absolute maximum ratings** (Ta=25°C)

Parameter	Ratings	Unit	
Gate to drain breakdown voltage	-15	V	
Gate to source breakdown voltage	-15	V	
Drain current	6	Α	
Reverse gate current	-18	mA	
Forward gate current	36	mA	
Total power dissipation	42.8	W	
Cannel temperature	175	°C	
Storage temperature	-65 to +175	°C	
	Gate to drain breakdown voltage Gate to source breakdown voltage Drain current Reverse gate current Forward gate current Total power dissipation Cannel temperature	Gate to drain breakdown voltage Gate to source breakdown voltage -15 Drain current 6 Reverse gate current -18 Forward gate current 36 Total power dissipation 42.8 Cannel temperature 175 Storage temperature -65 to +175	

\*1 : Tc=25°C

OUTLINE DRAWING Unit: millimeters (inches) 21.0 ± 0.3 (0.827 ± 0.012) (0.079MI  $0.6 \pm 0.15$  $(0.024 \pm 0.006)$ 12.9±0.2 (0.508±0.008) (0.445) R1.6 (R0.063) (0.079 MIN) 3 10.7 (0.421) 17.0 ± 0.2  $(0.102 \pm 0.008)$  $(0.669 \pm 0.008)$ 0.1(0.004)4.5±0.4 177±0.016) 12.0 (0.472) (T) GATE 2 SOURCE (FLANGE) GF-8 (3) DRAIN

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### Electrical characteristics (Ta=25°C)

Symbol	Parameter	Test conditions	Limits		Unit	
			Min.	Тур.	Max.	
IDSS	Saturated drain current	VDS=3V,VGS=0V	-	4	6	Α
gm	Transconductance	VDS=3V,ID=2.4A	1.2	2	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V,ID=20mA	-2	-	-5	V
P1dB	Output power at 1dB gain compression	VDS=10V,ID(RF off)=2.4A	38.5	39	-	dBm
GLP	Linear Power Gain	f=14.0 – 14.5GHz	4.5	5.5	-	dB
PAE	Power added efficiency		-	20	-	%
Rth(ch-c) *2	Thermal resistance	delta Vf method	-	-	3.5	°C/W

\*2 : Channel-case

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